

### Off-Line Quasi-Resonant Switching Regulators

#### **Features and Benefits**

- Quasi-resonant topology IC ⇒ Low EMI noise and soft switching
- Bottom-skip mode ⇒ Improved system efficiency over the entire output load by avoiding increase of switching frequency
- Standby mode ⇒ Lowers input power at very light output load condition
- Avalanche-guaranteed MOSFET  $\Rightarrow$  Improves system-level reliability and does not require  $V_{DSS}$  derating
- 450  $V_{DSS}$  / 0.189 Ω  $R_{DS(on)}$
- Various protections ⇒ Improved system-level reliability
- Pulse-by-pulse drain overcurrent limiting
- Overvoltage Protection (bias winding voltage sensing), with latch
- Overload Protection with latch
- Maximum on-time limit

### Package: 7-Pin TO-3P



Not to scale

### Description

The STR-X6729 is a quasi-resonant topology IC designed for SMPS applications. It shows lower EMI noise characteristics than conventional PWM solutions, especially at greater than 2 MHz. It also provides a soft-switching mode to turn on the internal MOSFET at close to zero voltage (V<sub>DS</sub> bottom point) by use of the resonant characteristic of primary inductance and a resonant capacitor.

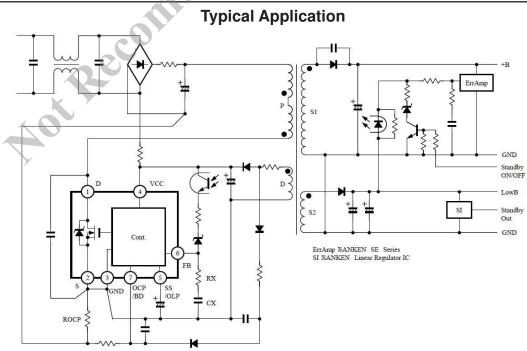
The package is a fully molded TO-3P, which contains the controller chip (MIC) and MOSFET, enabling output power up to 360 W at 120 VAC input. The bottom-skip mode skips the first bottom of  $V_{DS}$  and turns on the MOSFET at the second bottom point, to minimize an increase of operating frequency at light output load, improving system-level efficiency over the entire load range.

A standby mode is executed by clamping the secondary output. In general applications, standby mode reduces input power.

The soft-start mode minimizes surge voltage and reduces power stress to the MOSFET and to the secondary rectifying diodes during the start-up sequence.

Various protections such as overvoltage, overload, overcurrent, maximum on-time protections and avalanche-energy guaranteed MOSFET secure good system-level reliability.

Continued on the next page...



### Off-Line Quasi-Resonant Switching Regulators STR-X6729

### **Description (continued)**

Applications include the following:

- Set Top Box
- LCD PC monitor, LCD TV
- Printer, Scanner
- SMPS power supplies

### **Selection Guide**

Part Number	Package
STR-X6729	TO-3P

Selection Guide			Sign	•
Part Number	Packag	e		
STR-X6729	TO-3P		7	
Absolute Maximum Ratings at T <sub>A</sub> =				
Parameter	Symbol	Conditions	Rating	Unit
Drain Current <sup>1</sup>	I <sub>D</sub> peak	Single pulse	22	Α
Maximum Switching Current <sup>2</sup>	I <sub>Dmax</sub>	$T_A = -20^{\circ}\text{C to } 125^{\circ}\text{C}$	22	Α
Single Pulse Avalanche Energy <sup>3</sup>	E <sub>AS</sub>	Single pulse, $V_{DD}$ = 30 V, L = 50 mH, $I_{Lpeak}$ = 4.2 A	472	mJ
Input Voltage for Controller (MIC)	V <sub>CC</sub>		35	V
SS/OLP Terminal Voltage	V <sub>SSOLP</sub>	X	-0.5 to 6.0	V
FB Terminal Inflow Current	I <sub>FB</sub>	<b>A Y</b>	10	mA
FB Terminal Voltage	$V_{FB}$	I <sub>FB</sub> within the limits of I <sub>FB</sub>	-0.5 to 9.0	V
OCP/BD Terminal Voltage	V <sub>OCPBD</sub>	. 0	-1.5 to 5.0	V
MOSFET Power Dissipation <sup>4</sup>	P <sub>D1</sub>	With infinite heatsink	46	W
		Without heatsink	2.8	W
Controller (MIC) Power Dissipation	P <sub>D2</sub>	V <sub>CC</sub> × I <sub>CC</sub>	0.8	W
Operating Internal Leadframe Temperature	T <sub>F</sub>	Recommended operation temperature, see cautions	-20 to 125	°C
Operating Ambient Temperature	T <sub>OP</sub>		-20 to 125	°C
Storage Temperature	T <sub>stg</sub>		-40 to 125	°C
Channel Temperature	T <sub>ch</sub>	<u> </u>	150	°C

<sup>&</sup>lt;sup>1</sup>Refer to MOSFET ASO curve

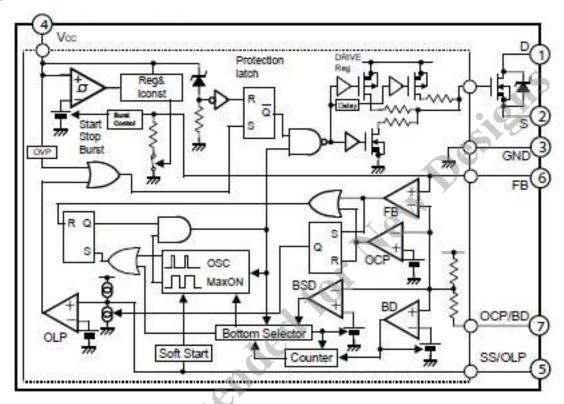
All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature, TA, of 25°C, unless otherwise stated.

<sup>&</sup>lt;sup>2</sup>I<sub>DMAX</sub> is the drain current determined by the drive voltage of the IC and the threshold voltage, V<sub>th</sub>, of the MOSFET

<sup>&</sup>lt;sup>3</sup>Refer to Avalanche Energy Derating curve

<sup>&</sup>lt;sup>4</sup>Refer to MOSFET Ta-PD1 curve

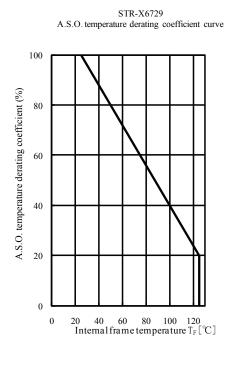
# Functional Block Diagram



### **Terminal List Table**

Number	Name	Description	Functions
1	D	Drain	MOSFET drain
2	S	Source	MOSFET source
3	GND	Ground terminal	Ground
4	VCC	Power supply terminal	Input of power supply for control circuit
5	SS/OLP	Soft Start/Overload Protection terminal	Input to set delay for Overload Protection and Soft Start operation
6	FB	Feedback terminal	Input for Constant Voltage Control and Burst (intermittent) Mode oscillation control signals
7	OCP/BD	Overcurrent Protection/Bottom Detection	Input for Overcurrent Detection and Bottom Detection signals

# Off-Line Quasi-Resonant Switching Regulators



MOS FET A.S.O. Curve

Ta=25°C Single Pulse

100

Determined by OnResistance
100µs

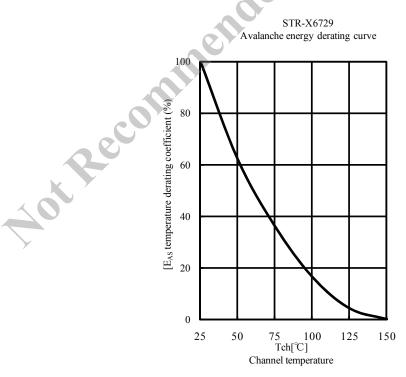
1 ms

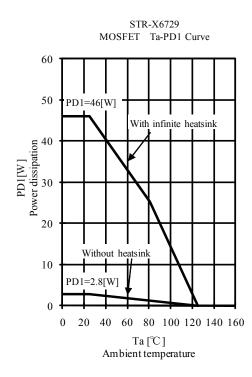
Apply ASO temperature
derating coefficient from the left graph to this curve for evaluating actual operation's safety

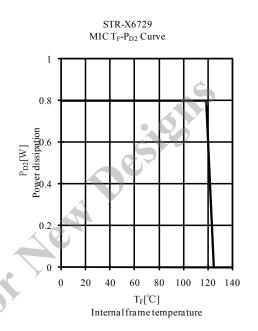
 $V_{DS}[V]$  Drain-to-Source Voltage

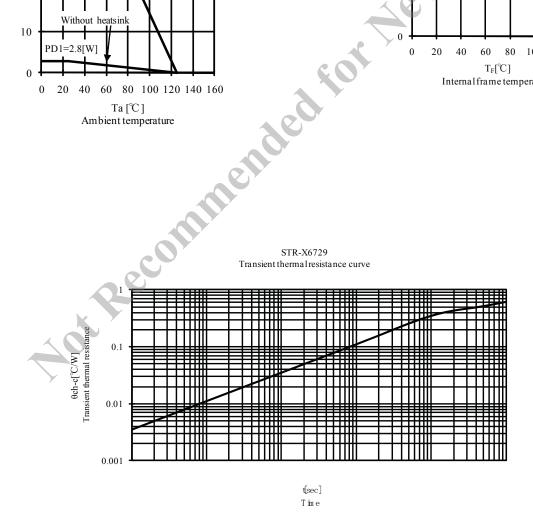
1000

STR-X6729









#### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
<b>ELECTRICAL CHARACTERISTICS for Controller (</b>	MIC) <sup>1</sup> , valid a	It $T_A = 25$ °C, $V_{CC} = 20$ V, unless othe	rwise spec	cified		
Power Supply Start-up Operation						
Operation Start Voltage	V <sub>CC(ON)</sub>	V <sub>CC</sub> = 0→20 V	16.3	18.2	19.9	V
Operation Stop Voltage	V <sub>CC(OFF)</sub>	V <sub>CC</sub> = 20→8.8 V	8.8	9.7	10.6	V
Circuit Current In Operation	I <sub>CC(ON)</sub>		_		6	mA
Circuit Current In Non-Operation	I <sub>CC(OFF)</sub>	V <sub>CC</sub> = 15 V	_		100	μA
Oscillation Frequency	f <sub>osc</sub>		19	22	25	kHz
Soft Start Operation Stop Voltage	V <sub>SSOLP(SS)</sub>	V <sub>SS/OLP</sub> increasing	1.1	1.2	1.4	V
Soft Start Operation Charging Current	I <sub>SSOLP(SS)</sub>	V <sub>SS/OLP</sub> = 0 V	-710	-550	-390	μA
Normal Operation						
Bottom-Skip Operation Threshold Voltage 1	V <sub>OCPBD(BS1)</sub>		-0.720	-0.665	-0.605	V
Bottom-Skip Operation Threshold Voltage 2	V <sub>OCPBD(BS2)</sub>		-0.485	-0.435	-0.385	V
Overcurrent Detection Threshold Voltage	V <sub>OCPBD(LIM)</sub>	V <sub>OCP/BD</sub> falling	-0.995	-0.940	-0.895	V
OCP/BD Terminal Outflow Current	I <sub>OCPBD</sub>	V <sub>OCP/BD</sub> = -0.95 V	-250	-100	-40	μA
Quasi-Resonant Operation Threshold Voltage 1	V <sub>OCPBD(TH1)</sub>	V <sub>OCP/BD</sub> falling	0.28	0.40	0.52	V
Quasi-Resonant Operation Threshold Voltage 2	V <sub>OCPBD(TH2)</sub>	V <sub>OCP/BD</sub> rising	0.67	0.80	0.93	V
FB Terminal Threshold Voltage	V <sub>FB(OFF)</sub>	V <sub>FB</sub> rising	1.32	1.45	1.58	V
FB Terminal Inflow Current (Normal Operation)	I <sub>FB(ON)</sub>	V <sub>FB</sub> = 1.6 V	600	1000	1400	μA
Standby Operation			,			
Standby Operation Start Voltage	V <sub>CC(S)</sub>	V <sub>CC</sub> = 0→15 V, V <sub>FB</sub> = 1.6 V	10.3	11.2	12.1	V
Standby Operation Start Voltage Interval	V <sub>CC(SK)</sub>	$V_{CC(SK)} = V_{CC(S)} - V_{CC(OFF)}$	1.10	1.35	1.65	V
Standby Non-Operation Circuit Current	Jcc(s)	V <sub>CC</sub> = 10.2 V, V <sub>FB</sub> = 1.6 V	_	20	56	μA
FB Terminal Inflow Current, Standby Operation	I <sub>FB(S)</sub>	V <sub>CC</sub> = 10.2 V, V <sub>FB</sub> = 1.6 V	_	4	14	μA
FB Terminal Threshold Voltage, Standby Operation	$V_{FB(S)}$	V <sub>CC</sub> = 15 V, V <sub>FB</sub> rising	0.55	1.10	1.50	V
Minimum On Time	t <sub>ON(MIN)</sub>		0.75	1.15	1.55	μs
Protection Operation			,			
Maximum On Time	t <sub>ON(MAX)</sub>		27.5	32.5	39.0	μs
Overload Protection Operation Threshold Voltage	V <sub>SSOLP(OLP)</sub>		4.0	4.9	5.8	V
Overload Protection Operation Charging Current	I <sub>SSOLP(OLP)</sub>	V <sub>SS/OLP</sub> = 2.5 V	-16	-11	-6	μA
Overvoltage Protection Operation Voltage	V <sub>CC(OVP)</sub>	V <sub>CC</sub> = 0→30 V	25.5	27.7	29.9	V
Latch Circuit Holding Current <sup>2</sup>	I <sub>CC(H)</sub>	V <sub>CC(OFF)</sub> - 0.3 V	_	45	140	μA
Latch Circuit Release Voltage <sup>2</sup>	V <sub>CC(La.OFF)</sub>	V <sub>CC</sub> = 30→6 V, OVP operating	6.0	7.2	8.5	V
ELECTRICAL CHARACTERISTICS for MOSFET, va	alid at T <sub>A</sub> = 25	°C, unless otherwise specified				
Drain-to-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>DSS</sub> = 300 μA	450	_	_	V
Drain Leakage Current	I <sub>DSS</sub>	V <sub>DSSS</sub> = 450 V	_	_	300	μA
On Resistance	R <sub>DS(on)</sub>	I <sub>DS</sub> = 4.0 A	_	_	0.189	Ω
Switching Time	t <sub>f</sub>		_	_	700	ns
Thermal Resistance	R <sub>0ch-F</sub>	Channel to internal frame	_	_	0.99	°C/W

<sup>&</sup>lt;sup>1</sup>Current polarity with respect to the IC: positive current indicates current sink at the terminal named, negative current indicates source at the terminal named.

<sup>&</sup>lt;sup>2</sup>The latch circuit means a circuit operated OVP and OLP.

### STR-X6729

### Off-Line Quasi-Resonant Switching Regulators

### Package Outline Drawing, TO-3P 15.6 ±0.2 5.5±0.2 Gate Burr 3.45±0.2 5.5±0. Ø3.2 ±0.2 Branding Area XXXXXXX xxxxxxx XXXXXXX 3.35±0.1 12.5±0.5 Terminal dimension at lead tip Terminal dimension at lead tip 1.33 +0.2 5X 0.75 <sup>+0.2</sup><sub>-0.1</sub> 2X 0.83 <sup>+0.2</sup><sub>-0.1</sub> 5X 0.65 <sup>+0.2</sup><sub>-0.1</sub> $1.89^{+0.2}_{-0.1}$ Enlargement View A

Gate burr: 0.3 mm (max.) Terminal core material: Cu

Terminal treatment: Ni plating and Pb-free solder dip

Leadform: 1902

Approximate weight: 6 g

Dimensions in millimeters

Drawing for reference only

Side View

Branding codes (exact appearance at manufacturer discretion):

1st line, type: STR
2nd line, subtype: X6729
3rd line, lot: YM DD

Where: Y is the last digit of the year of manufacture

M is the month (1 to 9, O, N, D)

DD is the 2-digit date



Leadframe plating Pb-free. Device composition includes high-temperature solder (Pb >85%), which is exempted from the RoHS directive.

Front View (Plan View)

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40% to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

#### **Cautions for Testing and Handling**

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

#### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting the products on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce excess stress.
- Volatile-type silicone greases may crack after long periods of time, resulting in reduced heat radiation effect. Silicone greases with low consistency (hard grease) may cause cracks in the mold resin when screwing the products to a heatsink.

Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Туре		Suppliers	
G746	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Shin-Etsu Chemical Co., Ltd.	
YG6260		Momentive Performance Materials Inc.	
SC102		Dow Corning Toray Co., Ltd.	

#### **Cautions for Mounting to a Heatsink**

When the flatness around the screw hole is insufficient, such
as when mounting the products to a heatsink that has an
extruded (burred) screw hole, the products can be damaged,
even with a lower than recommended screw torque. For
mounting the products, the mounting surface flatness should
be 0.05 mm or less.

- Please select suitable screws for the product shape. Do not
  use a flat-head machine screw because of the stress to the
  products. Self-tapping screws are not recommended. When
  using self-tapping screws, the screw may enter the hole
  diagonally, not vertically, depending on the conditions of hole
  before threading or the work situation. That may stress the
  products and may cause failures.
- Recommended screw torque: 0.588 to 0.785 N

  m (6 to 8 kgf

  cm).
- For tightening screws, if a tightening tool (such as a driver) hits the products, the package may crack, and internal stress fractures may occur, which shorten the lifetime of the electrical elements and can cause catastrophic failure. Tightening with an air driver makes a substantial impact. In addition, a screw torque higher than the set torque can be applied and the package may be damaged. Therefore, an electric driver is recommended.

When the package is tightened at two or more places, first pre-tighten with a lower torque at all places, then tighten with the specified torque. When using a power driver, torque control is mandatory.

### **Soldering**

- When soldering the products, please be sure to minimize the working time, within the following limits:
   260±5°C 10±1 s (Flow, 2 times)
  - 380±10°C 3.5±0.5 s (Soldering iron, 1 time)
- Soldering should be at a distance of at least 2.0 mm from the body of the products.

#### **Electrostatic Discharge**

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1 M $\Omega$  of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons
  or the solder bath must be grounded in order to prevent
  leak voltages generated by them from being applied to the
  products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil.

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